

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

WLJ.078

Application Number

10/018,809

Applicant(s)

Anand SRINIVASAN

Filing Date

12/21/2001

Group Art Unit

1763
~~TO BE ASSIGNED~~

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	CLASS	CLASS
gag	A	5,534,109	07/09/1996	FUJIWARA et al.			
gag	B	5,527,425	06/18/1996	HOBSON et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	CLASS	CLASS
gag	C	11-16896	01/22/1999	JAPAN			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

gag	D	C.F. CARLSTROM, et al., "Trimethylamine: Novel source for low damage reactive ion beam etching of InP" Journal of Vacuum Science and Technology B, vol. 17, no. 6, November 1999 (1999-11), pages 2660-2663, XP002150318
gag	E	ELKIND J L et al., "Reactive Ion Etching of HGCDTE with Methane and Hydrogen" Journal of Vacuum Science and Technology: Part A, US, American Institute of Physics. new York, vo. 10, no. 4, PT I, 1 July 1992 (1992-07-01), pages 1106-1112, XP000296215 ISSN: 0734-2101 page 1106, left-hand column, line 12-line 14.

EXAMINER

George Goudreau

DATE CONSIDERED

3-041

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.